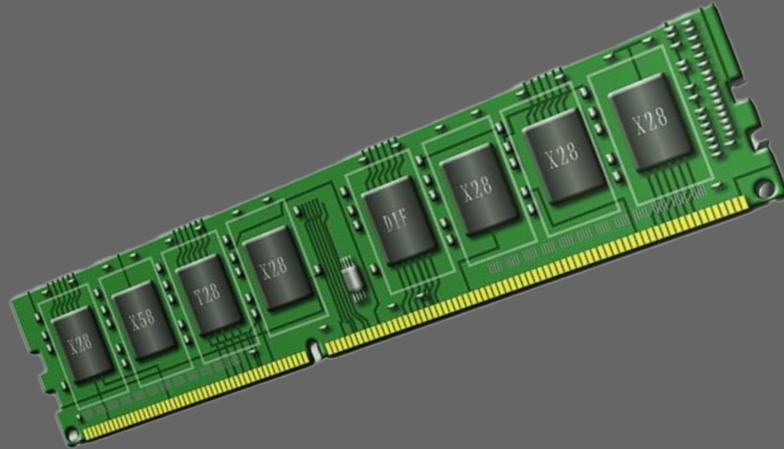


CPE 470 - RAM



RAM

- Used to Behavioral RAM in FPGA Land
 - reg [31:0] ram [1023:0];
- In ASIC Land, have to use IP
- Tradeoffs between capacity and latency
 - Fast memories → small
 - Large memories → slow
- Often Analog
 - Most Memory cells are analog structures
 - Exception: Registers/ Flip Flops

Technologies have vastly different tradeoffs between capacity, access latency, bandwidth, energy, and cost
 – ... and logically, different applications

	Capacity	Latency	Cost/GB
Register	1000s of bits	20 ps	\$\$\$\$
SRAM	~10 KB-10 MB	1-10 ns	~\$1000
DRAM	~10 GB	80 ns	~\$10
Flash*	~100 GB	100 us	~\$1
Hard disk*	~1 TB	10 ms	~\$0.10

* non-volatile (retains contents when powered off)

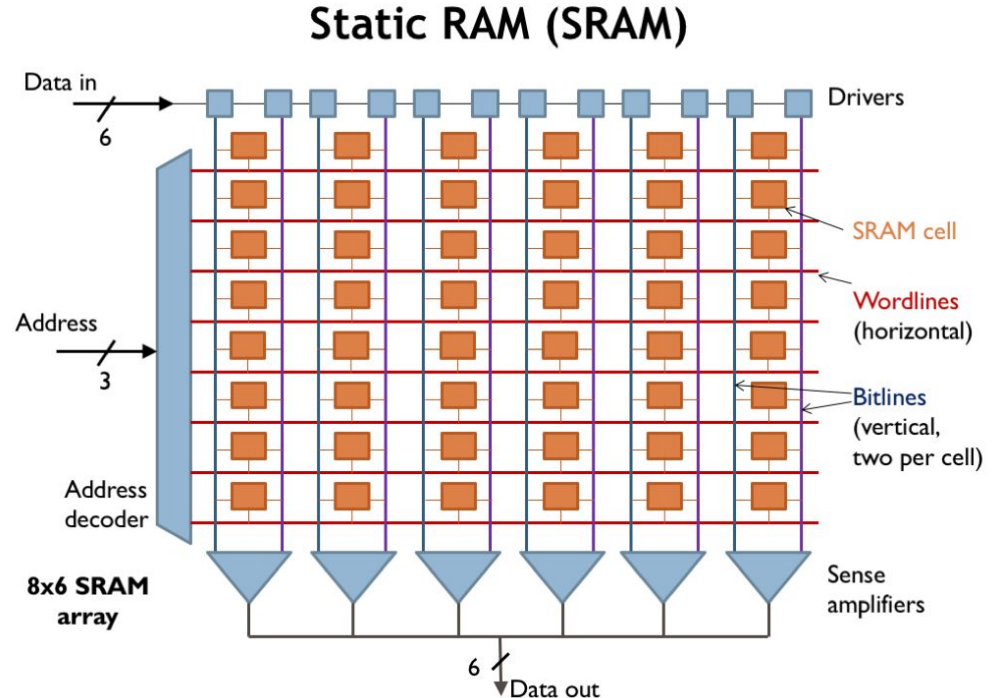
Processor
Datapath

Memory
Hierarchy

I/O
subsystem

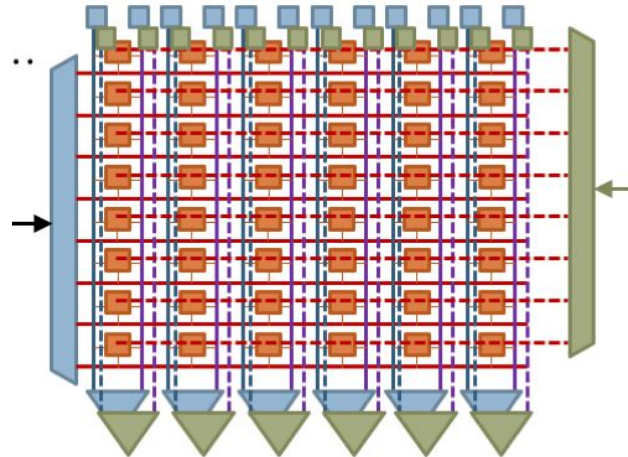
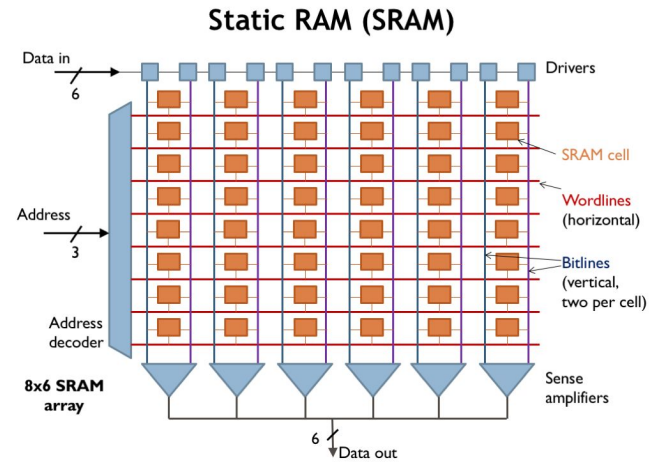
SRAM

- Fastest On-Chip RAM
 - Except for flip flops which are not RAM
- Volatile Memory
 - Stores data as long as power is supplied
- 6 transistors per bit cell
 - Useful as a metric of size
 - More transistors = less dense
- Analog
 - Requires sense amplifiers to read each bit
 - Must be simulated with behavioral model, not gate-level



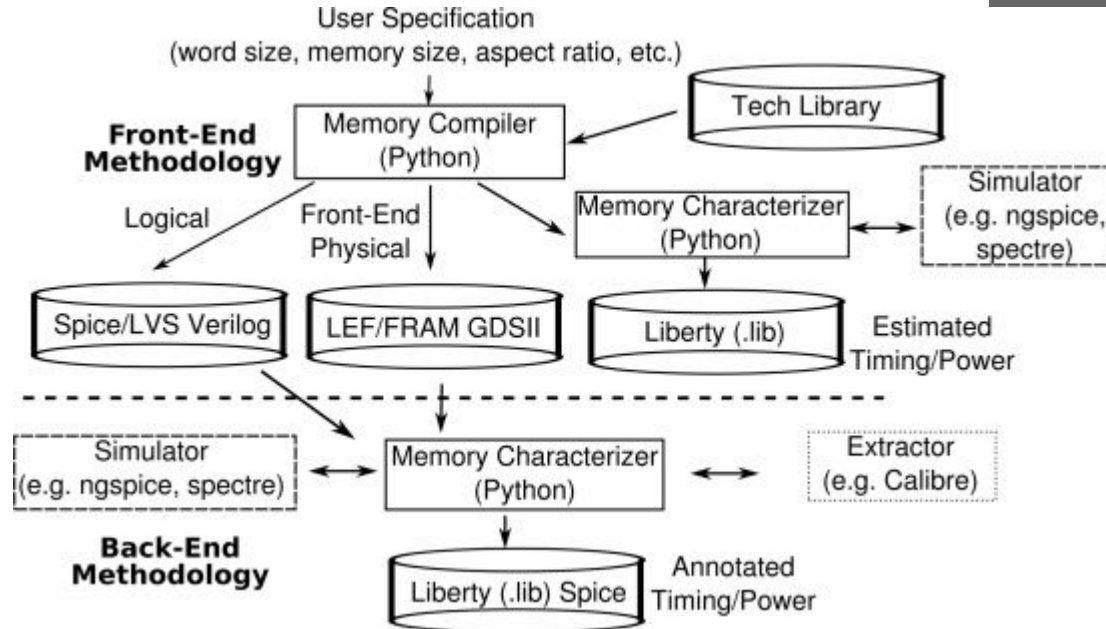
SRAM - Ports

- Adding more access ports is expensive
 - Scaling from 1 to 2 ports doubles amount of wires
- Wires are often limiting factor
 - Leads to $\sim n^2$ scaling for adding ports
- SRAMs with more ports are often less dense, harder to find



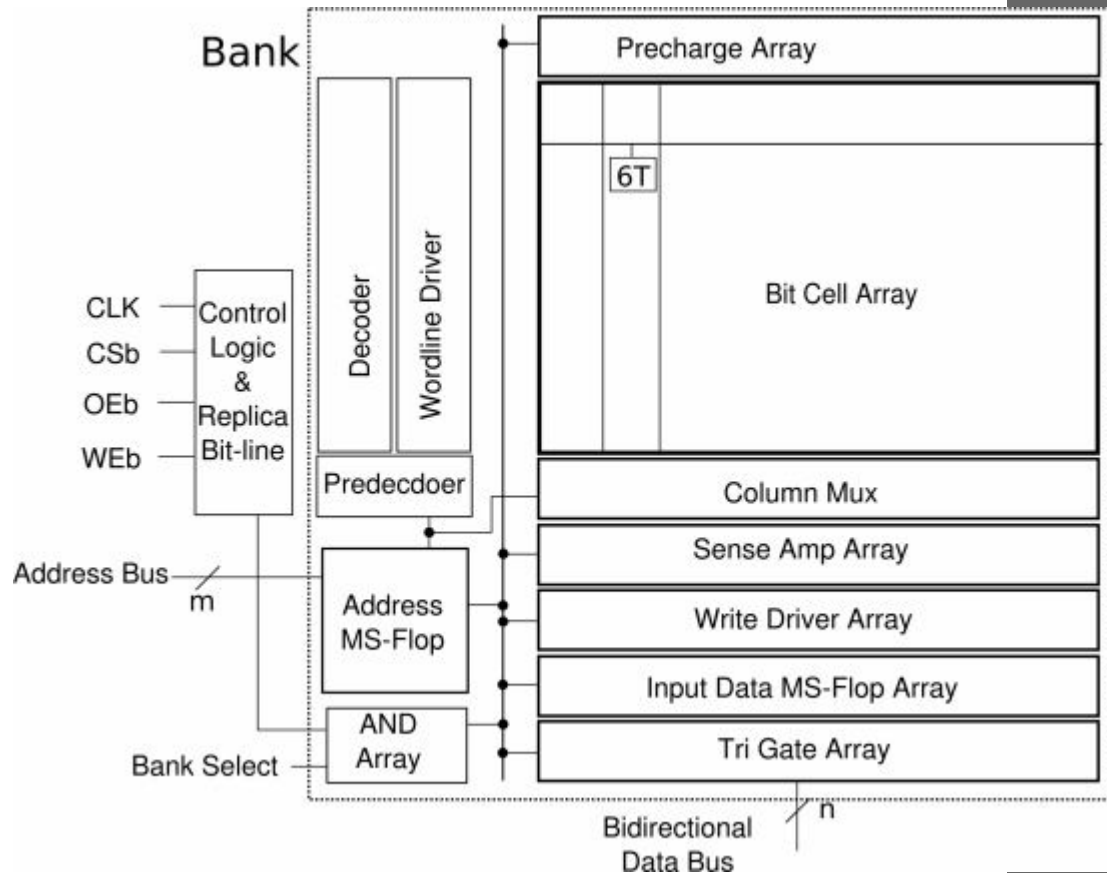
Ram Compilers

- How do we design RAM to fit our needs?
 - What if there is not pre-existing IP for our use case?
- Solution: Ram Compilers
 - RAM is made of repetitive structures
 - Copy analog structures automatically
- Characterizes RAM
 - Generates SPICE and simulates electrically
 - Creates timing file (.lib)
 - Creates verilog models



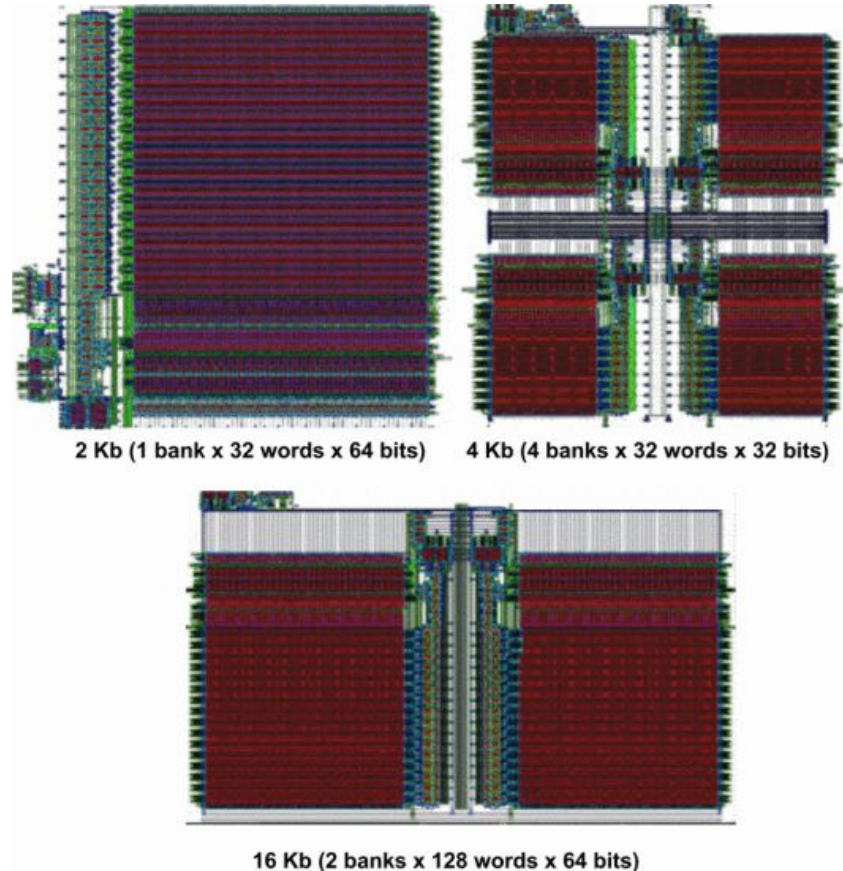
OpenRAM

- Many RAM compilers are highly expensive
 - Good RAM is valuable IP
- OpenRAM → Open Source alternative
- Breaks RAM down into basic elements
 - Sense Amps to Read, Address Decoders, etc.
 - Not PDK specific



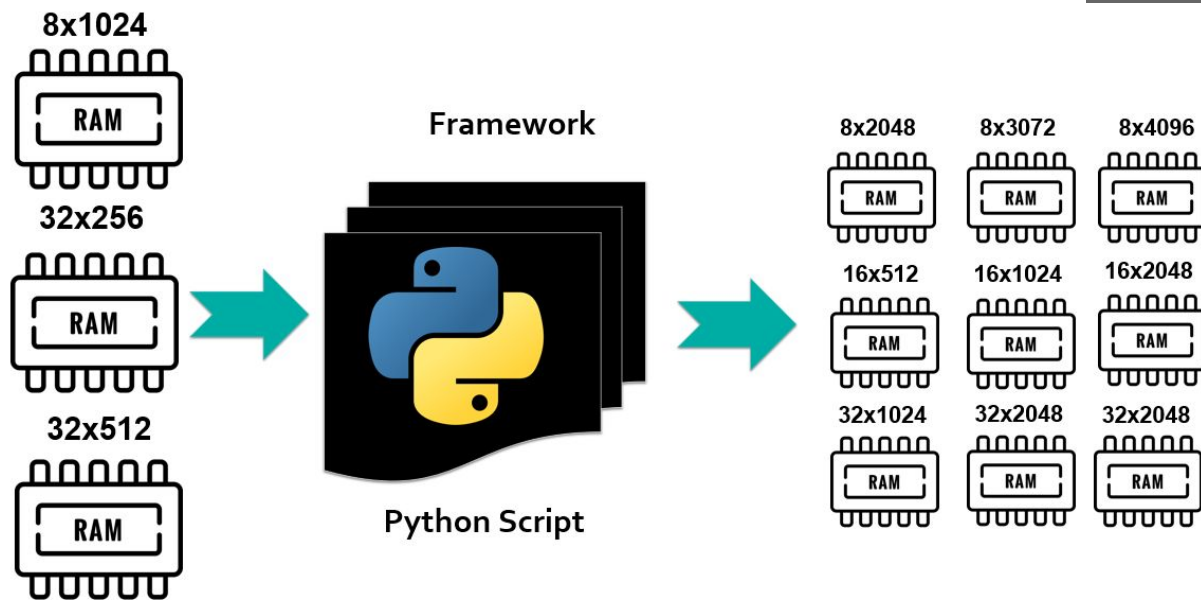
OpenRAM

- User/Community implements most basic modules
 - Each PDK needs its own implementation
- Compiler arranges and scales modules based on input sizes
 - Always a power of 2
- Outputs spice, gds, etc.



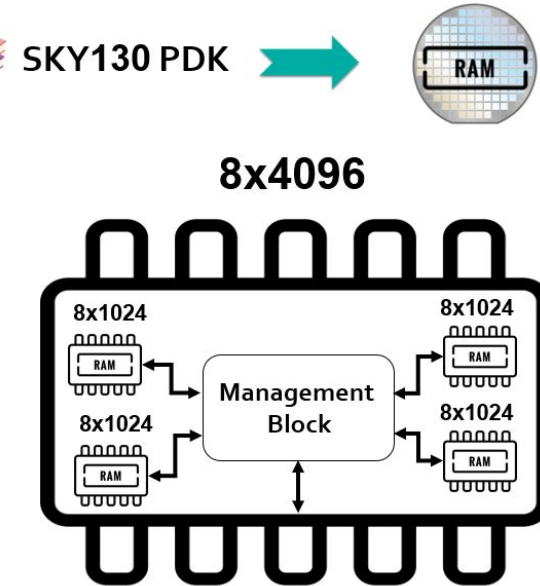
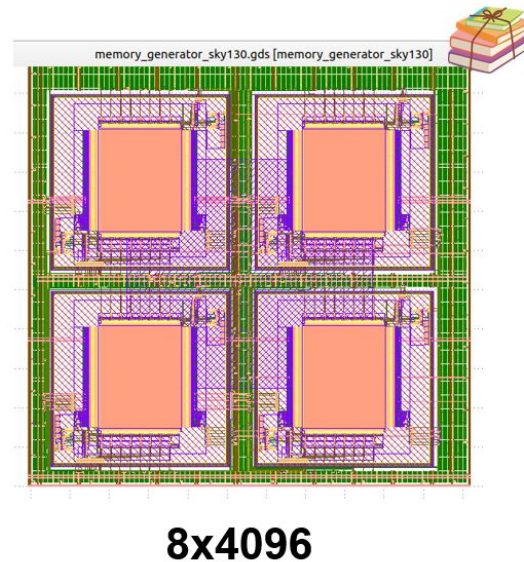
Ram Layout & Interleaving Tools

- Sometimes SRAM compilers are not enough
 - Almost always limited to powers of 2 for size and width
 - Compiling your own SRAM is difficult
- Solution: Combine existing IP into new sizes
 - Ram Layout tools help combine modules into new sizes



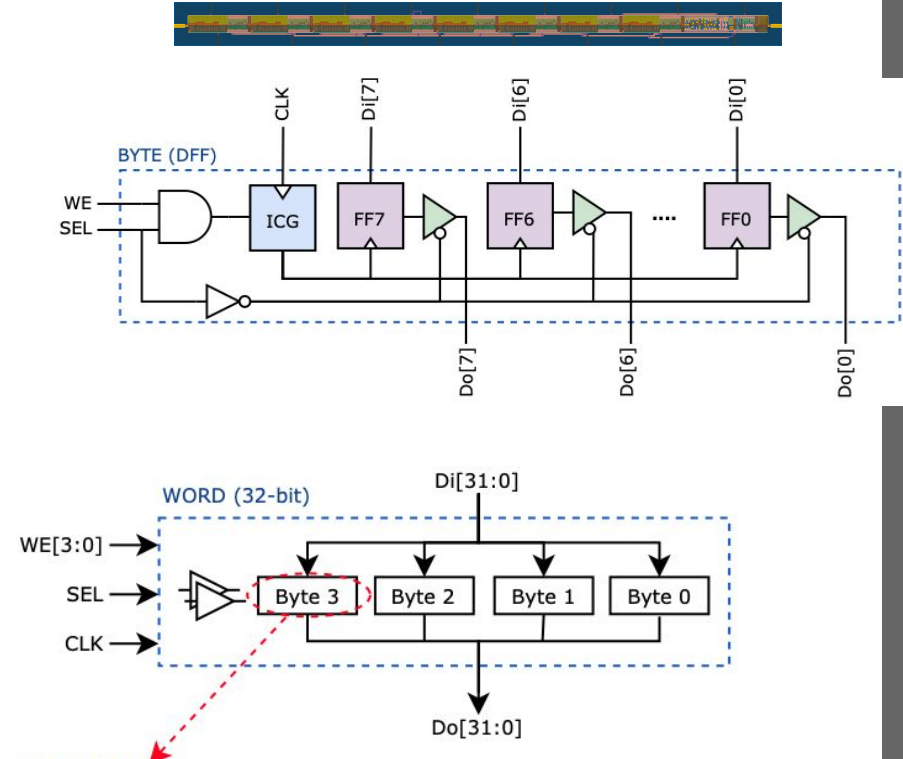
Ram Layout Tools

- Solution: Combine existing IP into new sizes
 - Ram Layout tools help combine modules into new sizes
- Tools create:
 - Interconnects between rams in verilog
 - Macro positions
- Can scale to non powers of 2



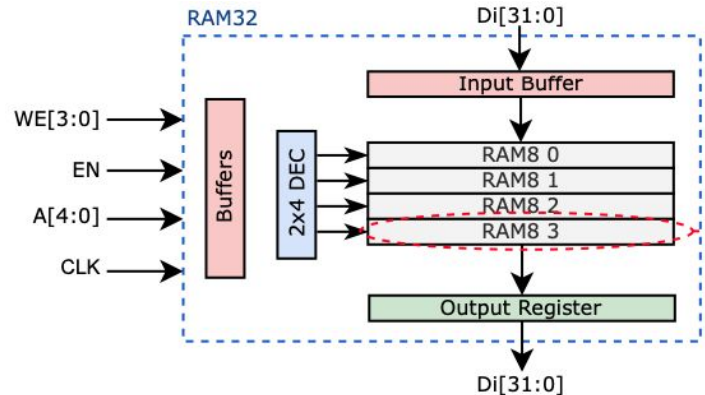
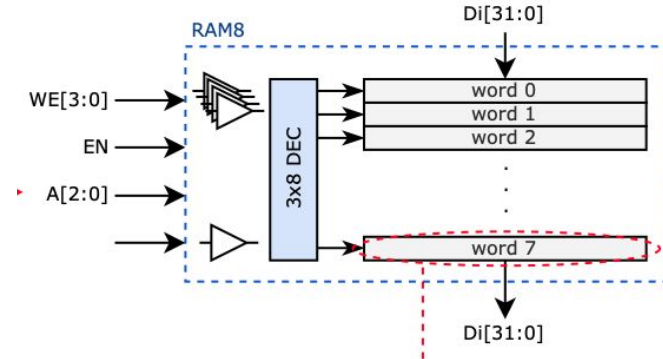
DFFRAM

- Problem 1: SRAM is hard to validate
 - Simulation is done with behavioral model, not actual hardware
- Problem 2: SRAM doesn't work on OpenLane2
 - Only works on OpenLane1
- Solution: DFFRAM
 - Array of Densely Packed Flip Flops
 - Purely digital (no analog elements)
 - Can do gate-level simulation of cells
- 20-30 Transistors per Bit
 - ~5x worse density than SRAM
 - ~5x better than declaring a 2d array in verilog



DFFRAM - Scaling Up

- Built using Recursive Macros
 - 8 DFFs make a byte, 4 bytes make a word
 - Words are stacked vertically to make rams
 - 8 Words Stacked makes a RAM8
 - 2 RAM8s make a RAM16, etc.
- Provides macros generally up 512 words (2 KB)
 - Most have 1 read/write port
 - Some have 2 ports but on the smaller end of capacity



DRAM

- 1 Transistor per Bit
 - At least 6x denser than SRAM
- Highest Density Ram Available
 - Not usable on SKY130
 - Generally requires specific PDK
 - Often used off-chip
- Destructive Reads
 - Bits can only be read once
 - Have to re-write after each read
- Requires Refreshes
 - Bits last temporarily
 - Have to be refreshed every milliseconds

Glossary

DRAM: Dynamic RAM

SDRAM: Synchronous DRAM

DDR: Double Data Rate

DDR RAM



Also DDR RAM

“I don’t think the highest density ram would be very good at DDR”



SONOS Flash

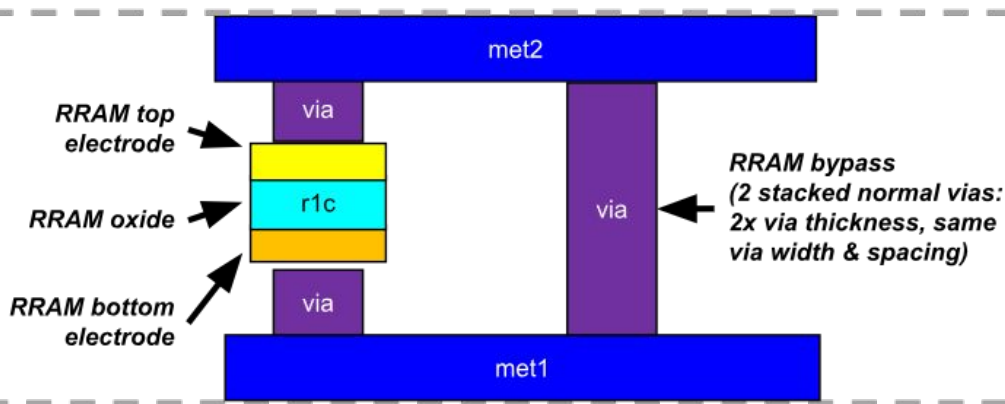
- Non-Volatile Flash Memory On Chip!
 - Supported by SKY130!
- Problem: requires fancy voltages to read and write
 - On the order of +10 and -3 volts
 - Usually digital chip only has +3.3 and +1.8 volts
 - Available as an analog cell
 - Yet to be wrapped in a usable macro



RRAM / ReRAM

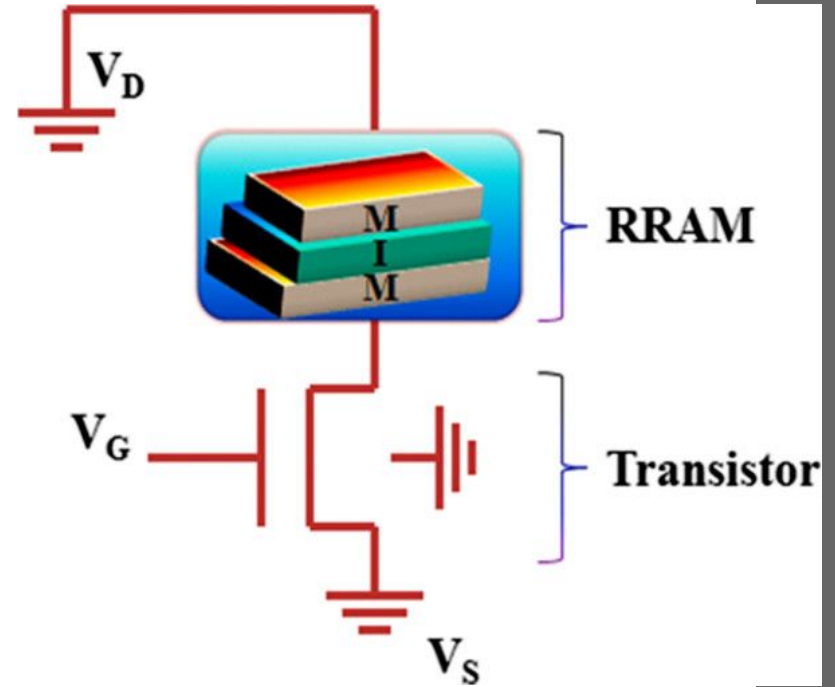
- Store values in the resistance of a conductor
 - 1 -> Low Resistance
 - 0 -> High Resistance
- Use material that changes its resistance in an electric field
 - Resistance responds to voltage
 - Can be implemented vertically on chip
- Set/Reset using different voltages
- Read by Measuring Current
 - High Current → 1

RRAM between met1/met2



RRAM Advantages

- + Higher Density than SRAM
 - 1 transistor per bit
- + Reads are efficient
 - Low latency
 - Low energy
- + Non-Volatile
 - Holds resistive state on reset
 - Easier voltages than SONOS
- + Can sometimes hold multiple bits per cell



RRAM Disadvantages

- Higher write latency than read latency
 - Writes involve physical structure change
- Limited endurance compared to volatile technologies (SRAM, DRAM)
 - Finite number of writes
- Misbehaves at very high temperatures
 - Changes resistance

MRAM

- Non Volatile, Similar to RRAM
 - Uses magnetic fields instead of electric fields to change resistance
 - Write by using the magnetic field of a current
- + Generally more reliable than RRAM
 - + More write cycles
 - + Not as sensitive to temperature
- More expensive and less dense than RRAM
- Sensitive to magnetic fields

References

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- <https://github.com/Baungarten-CINVESTAV/SKY130-Macro-Memory-Cell-Generator>
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